

NAK1-BK00



PATENT APPLICATION

#71A  
Bell  
W31er

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Toshiya Fukuhisa, et al.

Serial No. 09/515,285

Filed: February 29, 2000

For: SEMICONDUCTOR LASER AND A  
MANUFACTURING METHOD FOR THE  
SAME

Examiner: Tuan M. Nguyen

Group Art Unit: 2828

October 23, 2002

Irvine, California 92614

RESPONSE TO OFFICE ACTION

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Office Action mailed July 31, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please add the following new claims:

- 1 37. (New) A semiconductor laser according to Claim 2,  
2 wherein the second layer is co-doped with p-type impurities and n-  
3 type impurities and has substantially n-type conductivity, and such that the concentration  
4 of n-type carriers is N2.
- 1 38. (New) A semiconductor laser manufacturing method according to Claim  
2 26,  
3 wherein the first process co-dopes the second layer with p-type  
4 impurities and n-type impurities, such that the concentration of n-type carriers is N2.

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